

ABSTRACT

A method of forming minimally spaced word lines is disclosed. A double exposure technique is employed at the gate formation level. A small trench is defined through gate stack layers by using a tapered etch or spacers to achieve the desired width of the trench. A filler material fills the trench and forms a filler plug. The gate layers adjacent to the trench are then patterned and etched and the filler plug is removed to obtain gate stacks spaced apart by a distance of less than about 400 Angstroms.

10